

EAST: [10644902 buried source line.wsp:1]

File View Edit Tools Window Help

Pending

Active

L1: (56) (buried near (conduct\$4 source adj line) (bl bitline bit adj line readline read

L2: (13) ((buried embedded) near2 (bl bitline bit adj line readline read adj line sense a

L3: (68) 1 2

Failed

Saved

(1) 09/948877

(1738) "KONINKLIJKE PHILIPS".as

(0) 10/644902

(532) "MACRONIX INTERNATIONAL".as

(21575) source adj line

(527358) (FOX field adj oxide STI (isolat\$3 (element adj (insulat\$4 separat\$4)) a

(133613) buried

(848972) (bl bitline bit adj line readline read adj line sense adj line column)

(21575) source adj line

(527358) (FOX field adj oxide STI (isolat\$3 (element adj (insulat\$4 separat\$4)) a

(133613) buried

(848972) (bl bitline bit adj line readline read adj line sense adj line column)

(3873) buried near (conduct\$4 source adj line) (bl bitline bit adj line readline read ar

(244) (buried near (conduct\$4 source adj line) (bl bitline bit adj line readline read adj

(56) ((buried near (conduct\$4 source adj line) (bl bitline bit adj line readline read adj

(2850140) (conduct\$4 source adj line) (bl bitline bit adj line readline read adj line se

(58) ((buried near (conduct\$4 source adj line) (bl bitline bit adj line readline read adj

(87889) (bl bitline bit adj line)

(21621) source adj line 1 near4 (bl bitline bit adj line 10)

Browse Queue Clear

DBs: USPAT-US PGPUB:EPO:JPO:DERWENT:IBM:TD0

Default operator: CR

Plurals

Highlight all hit terms initially

1 2

July 2007

ASRQ form ASRQ form Change Text HTML

	U	T	Investor	Document#	Issue#	P	Title	Current	Current X	Retrieval	S	C	P	4	5	Image	Doc.	P
1			Lee, Robin	US 6372584	20020:9		Method of manufacturing V-shaped flash me	438/192/257/E29.30									US 637258	
2			Sheu, Shing	US 6380587	20020:1		Semiconductor read-only memory device and	257/330/257/303									US 638058	
3			Lee, Claymen	US 6153471	20001:1		Method of fabricating flash memory	438/283/257/E21.68									US 615347	
4			Gill, Manzur	US 5420060	19950:1		Method of making contact-free floating gat	438/261/257/E21.68									US 542006	
5			Fan, Der-Tsy	US 2004013	20040:3		Flash memory with trench select gate end fa	365/185/365/51									US 200401	
6			Gonzalez, Fer	US 2004004	20040:2		Vertically integrated flash memory cell and	257/315									US 200400	
7			Ramsbey, Me	US 2003008	20030:1		SALICIDED GATE FOR VIRTUAL GROUND AR	257/286/257/E21.64									US 200300	
8			Hsueh, Cheng	US 2002017	20021:6		Method of fabricating mask read only memor	438/278/257/E21.67									US 200201	
9			Lee, Robin	US 2002000	20020:9		V-shaped flash memory structure	257/314/257/E29.30									US 200200	
10			Rhodes, How	US 6740915	20040:1		CMOS imager cell having a buried contact	257/291/257/282									US 674091	

Ready